IN THE SPECIFICATION

Please replace the paragraph beginning on page 4, line 15 and ending on line 20 with the following amended paragraph:

According to such a structure, the concave portion is only formed on the translucent substrate. Consequently, the concave portion can be formed to easily have a gap ~~0opposite~~ opposite to each light receiving region. Therefore, the number of components can be decreased and the manufacture can easily be carried out.

Please replace the paragraph beginning on page 35, line 2 with the following amended paragraph:

In the IT-CCD, a channel stopper 28 is provided in a p well 101b formed on the surface of an n-type silicon substrate 101a, and a photodiode 14 and an electric charge transfer element 33 are formed with the channel stopper 28 interposed therebetween. Herein, ~~an n-type impurity~~ a p+ channel (p-type impurity) region 14b is provided in a ~~p+ channel~~ n-type impurity region 14a to form the photodiode 14. Moreover, a vertical charge transfer channel 20 comprising an n-type impurity region having a depth of approximately 0.3μm is formed in the ~~p+ channel~~ well region ~~14a,~~ 101b and a vertical charge transfer electrode 32 comprising a polycrystalline silicon layer is formed on the vertical charge transfer channel 20 through a gate insulating film 30 comprising a silicon oxide film so that an electric charge transfer element 33 is constituted. Moreover, a channel 26 for a reading gate is

formed by the p-type impurity region between the electric charge transfer element 33 and the photodiode 14 on the side where a signal charge is read onto the vertical charge transfer channel 20.

Please replace the paragraph beginning on page 123, line 2 and ending on line 14 with the following amended paragraph:

Next, description will be given to a process for manufacturing the solid-state imaging device. This method is based on a so-called wafer level CSP method in which positioning is carried out on a wafer level, collective mounting and integration are performed and isolation for each IT-CCD is then executed as shown in views illustrating the manufacturing process in Figs. 54A to ~~2F~~ E and Fig. 55A to ~~3E~~ E (only one unit is shown in the drawing and a plurality of IT-CCDs are continuously formed on one wafer). This method is characterized by the use of a sealing cover glass 200 having a spacer which is provided with a spacer 203S in advance and a through hole penetrating through the glass substrate and the spacer.

Please replace the paragraph beginning on page 139, line 5 and ending on line 15 with the following amended paragraph:

On the other hand, the IT-CCD substrate 100 provided with a reinforcing plate 701 is prepared as shown in Fig. 63(b) ~~Fig. 3(b)~~. In the formation of the element substrate, as shown in Fig. 63(b) ~~Fig. 3(b)~~, the silicon substrate 101 (a 4 to 8 inch wafer is used) is prepared in advance (only one unit is shown in the drawing and a plurality of IT-CCDs are continuously formed on one wafer). It is also possible to easily carry out division after the mounting by a method of forming, through etching, a cut trench in a region corresponding to a dividing line for division into each IT-CCD over the surface of the silicon substrate 101.

Please replace the paragraph beginning on page 139, line 23 and ending on page 140, line 6 with the following amended paragraph:

As shown in Fig. 63(c) ~~Fig. 3(c)~~, thereafter, an alignment is carried out with an alignment mark formed in the peripheral edge portion of each substrate, and the sealing cover glass 220 having the lens array to which the spacer 203S is bonded is mounted on the IT-CCD substrate 100 provided with the element region as described above, and heating is carried out to integrate both of them with the adhesive layer 207. It is desirable that this step should be executed in a vacuum or an inert gas atmosphere such as a nitrogen gas.

Please replace the paragraph beginning on page 146, line 16 and ending on line 21 with the following amended paragraph:

As shown in a sectional view of Fig. ~~81A~~ 71A and an enlarged sectional view showing a main part in Fig. ~~81B~~ 71B, a solid-state imaging device has such a structure that a sealing cover glass itself is caused to have condensing and image forming functions to constitute an optical member. Consequently, a size can be more reduced.

Please replace the paragraph beginning on page 151, line 7 and ending on line 8 with the following amended paragraph:

As shown in Fig. 80 ~~Fig. 90~~, moreover, it is also effective that a wiring 221 is formed on the side wall of a spacer.